

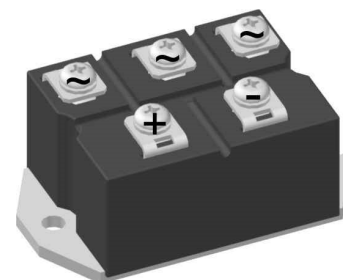
Standard Rectifier Module

3~ Rectifier	
V_{RRM}	= 1800 V
I_{DAV}	= 90 A
I_{FSM}	= 750 A

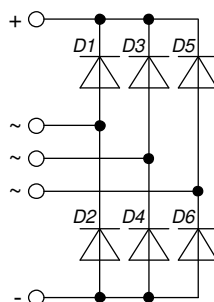
3~ Rectifier Bridge

Part number

VUO82-18NO7



 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: PWS-D

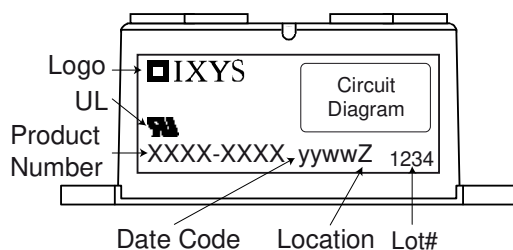
- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Disclaimer Notice

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1900	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1800	V
I_R	reverse current	$V_R = 1800\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			100	μA
		$V_R = 1800\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			1.5	mA
V_F	forward voltage drop	$I_F = 30\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.08	V
		$I_F = 90\text{ A}$				1.35	V
		$I_F = 30\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			0.99	V
		$I_F = 90\text{ A}$				1.33	V
I_{DAV}	bridge output current	$T_C = 115^{\circ}\text{C}$ rectangular	$T_{VJ} = 150^{\circ}\text{C}$ $d = \frac{1}{3}$			90	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		0.78	V
r_F	slope resistance					6	m Ω
R_{thJC}	thermal resistance junction to case					0.9	K/W
R_{thCH}	thermal resistance case to heatsink				0.4		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				135	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			750	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			810	A
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			640	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			690	A
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			2.82	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			2.73	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			2.05	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			1.98	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$			27		pF

Package PWS-D			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal			150	A
T _{VJ}	virtual junction temperature		-40		150	°C
T _{op}	operation temperature		-40		125	°C
T _{stg}	storage temperature		-40		125	°C
Weight				159		g
M _D	mounting torque		4.25		5.75	Nm
M _T	terminal torque		4.25		5.75	Nm
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal	9.5			mm
d _{Spb/Apb}		terminal to backside	26.0			mm
V _{ISOL}	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V
		50/60 Hz, RMS; I _{ISOL} ≤ 1 mA				

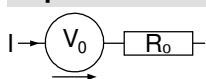


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO82-18NO7	VUO82-18NO7	Box	10	502555

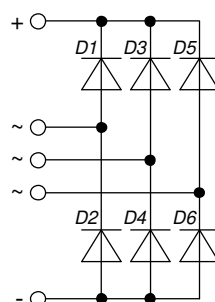
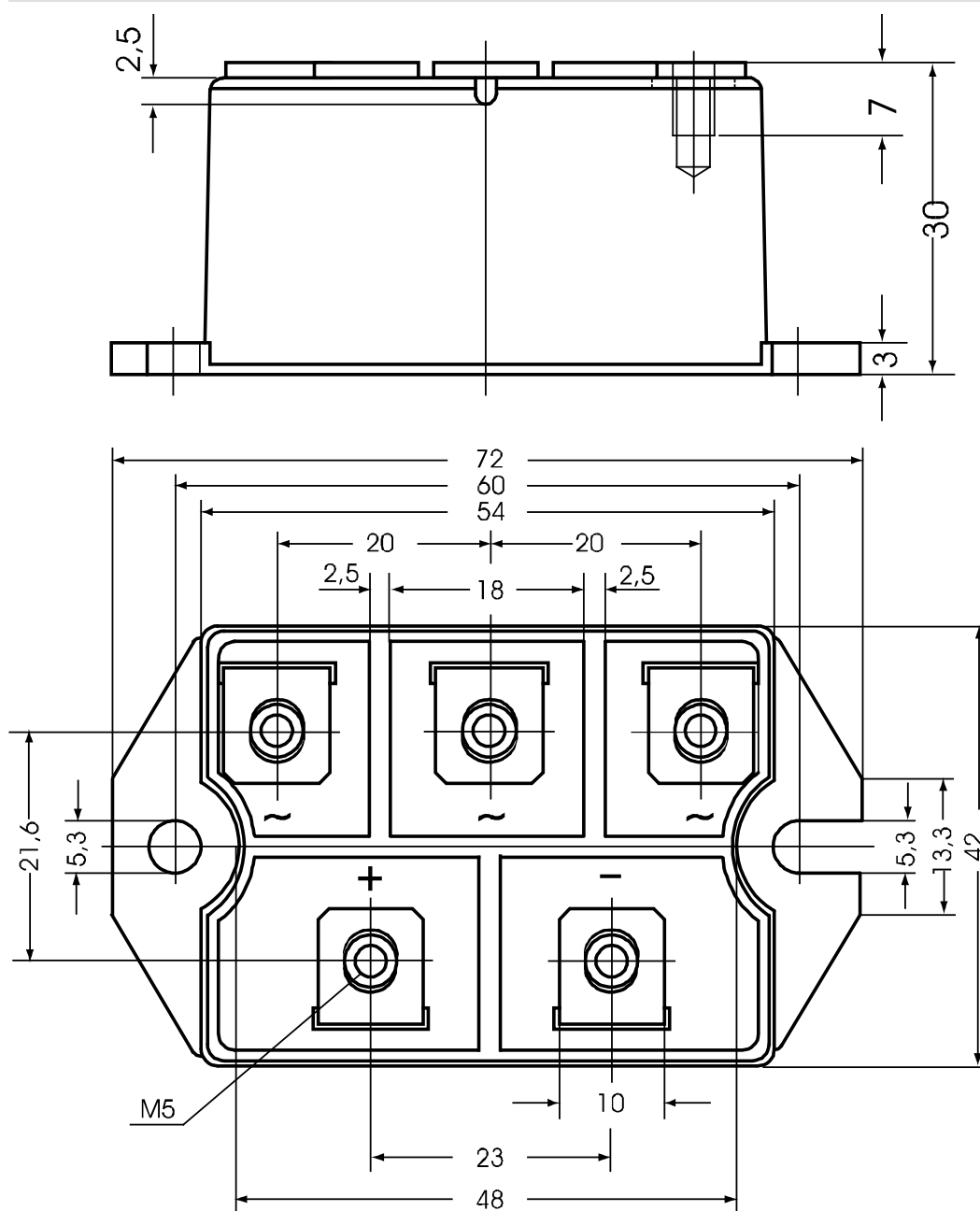
Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}\text{C}$

		Rectifier	
$V_{0\max}$	threshold voltage	0.78	V
$R_{0\max}$	slope resistance *	4.8	mΩ

Outlines PWS-D



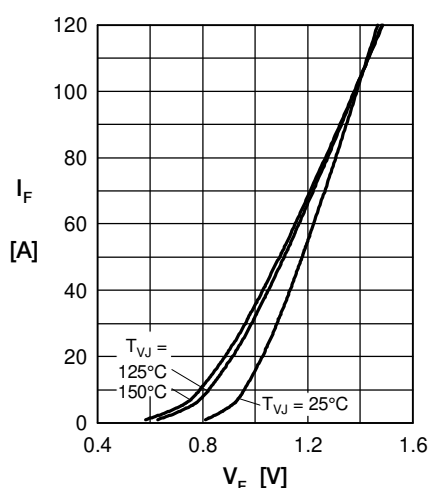
Rectifier


Fig. 1 Forward current versus voltage drop per diode

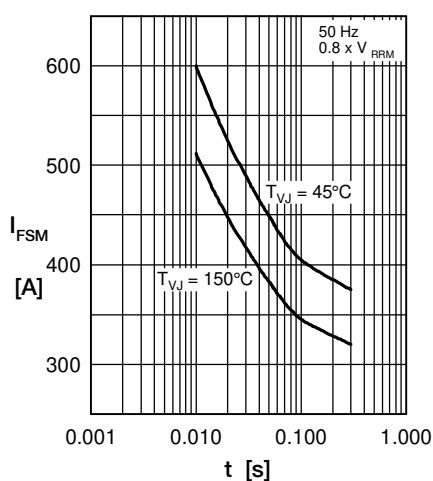


Fig. 2 Surge overload current

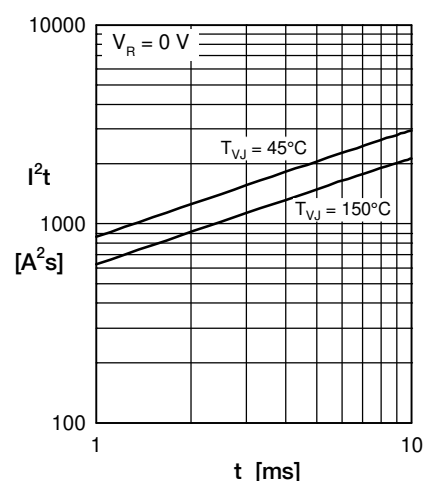
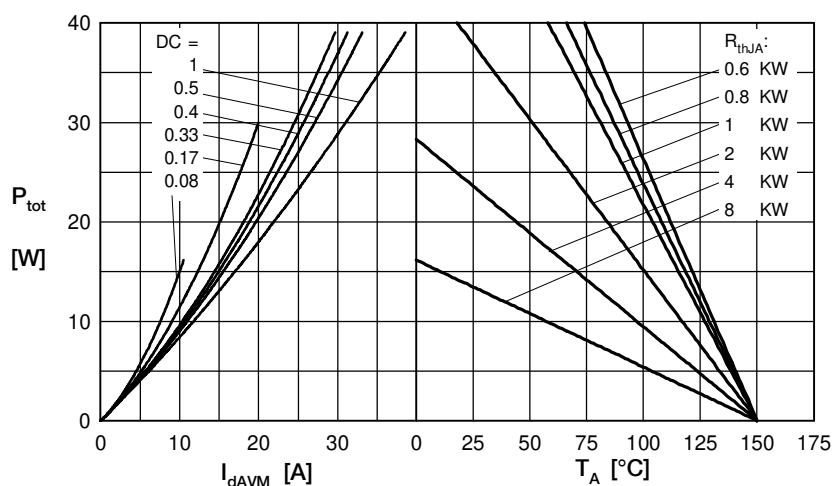

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation vs. direct output current & ambient temperature

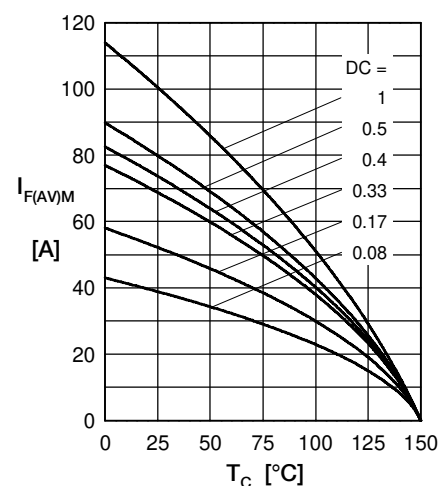


Fig. 5 Max. forward current vs. case temperature

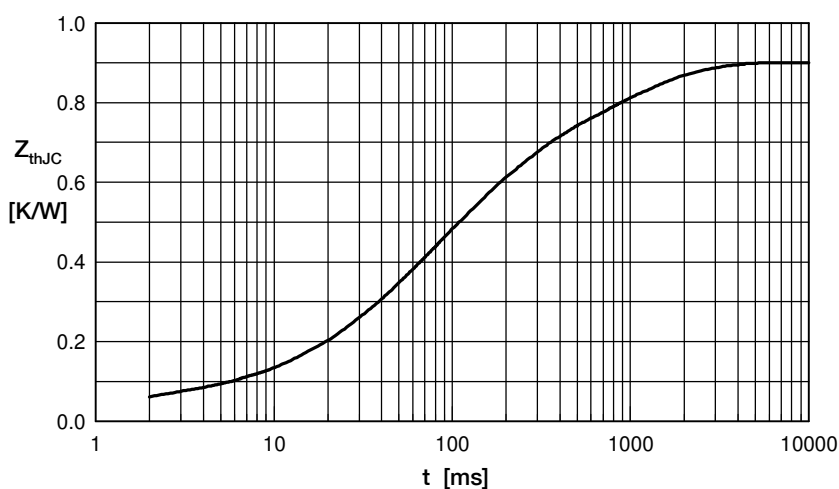


Fig. 6 Transient thermal impedance junction to case

 Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.05	0.001
2	0.14	0.030
3	0.18	0.070
4	0.28	0.150
5	0.25	0.950